

ABSTRACT OF THE DISCLOSURE

A method of manufacturing a semiconductor device using a polishing slurry for CMP of Cu, which includes a first complexing agent containing a heterocyclic compound which is capable of forming a water-insoluble complex with Cu, and a second complexing agent containing a heterocyclic compound which is capable of forming a slightly water-soluble or water-soluble complex with Cu to thereby provide at least one extra ligand subsequent to formation of the complex.